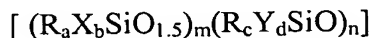


## IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A process for producing low-k dielectric films on semiconductors or electrical circuits, which comprises using incompletely condensed polyhedral oligomeric silsesquioxanes of the formula



with:

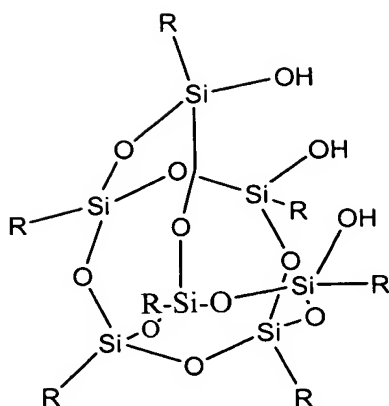
a, b=0-1; c, d=1; m+n ≥ 3; a+b=1; n, m ≥ 1,

R = hydrogen atom or alkyl, cycloalkyl, alkenyl, cycloalkenyl, alkynyl, cycloalkynyl, aryl or heteroaryl group, in each case substituted or unsubstituted,

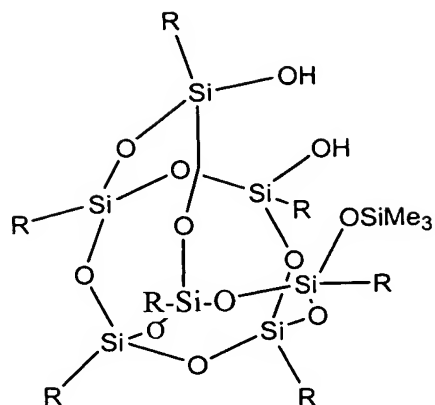
X = an oxy, hydroxyl, alkoxy, carboxyl, silyl, silyloxy, halogen, epoxy, ester, fluoroalkyl, isocyanate, acrylate, methacrylate, nitrile, amino or phosphine group or substituents of type R containing at least one such group of type X,

Y = hydroxyl, alkoxy or a substituent of type O-SiZ<sub>1</sub>Z<sub>2</sub>Z<sub>3</sub>, where Z<sub>1</sub>, Z<sub>2</sub> and Z<sub>3</sub> are fluoroalkyl, alkoxy, silyloxy, epoxy, ester, acrylate, methacrylate or a nitrile group or substituents of type R and are identical or different,

not only the substituents of type R being identical or different but also the substituents of type X and Y in each case being identical or different, and comprising at least one hydroxyl group as substituent of type Y, for producing the film and wherein incompletely condensed polyhedral oligomeric silsesquioxanes of structure 1 or 2



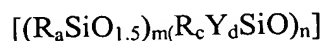
1



2

are used.

Claim 2 (Original): The process as claimed in claim 1, wherein incompletely condensed polyhedral oligomeric silsesquioxanes of the formula



with:

a, c, d=1; m+n ≥ 3; n, m ≥ 1,

R = hydrogen atom or alkyl, cycloalkyl, alkenyl, cycloalkenyl, alkynyl, cycloalkynyl, aryl or heteroaryl group, in each case substituted or unsubstituted,

Y = hydroxyl, alkoxy or a substituent of type O-SiZ<sub>1</sub>Z<sub>2</sub>Z<sub>3</sub>, where Z<sub>1</sub>, Z<sub>2</sub> and Z<sub>3</sub> are fluoroalkyl, alkoxy, silyloxy, epoxy, ester, acrylate, methacrylate or a nitrile group or substituents of type R and are identical or different,

not only the substituents of type R being identical or different but also the substituents of type Y in each case being identical or different, and comprising at least one hydroxyl group as substituent of type Y, are used.

Claim 3 (Currently Amended): The process as claimed in claim 1 ~~or 2~~, wherein incompletely condensed polyhedral oligomeric silsesquioxanes containing not more than three hydroxyl groups as type Y substituent are used.

Claim 4 (Currently Amended): The process as claimed in ~~at least one of claims 1 to 3~~ claim 1, wherein incompletely condensed polyhedral oligomeric silsesquioxanes are reacted with alkoxysilanes.

Claim 5 (Original): The process as claimed in claim 4, wherein incompletely condensed polyhedral oligomeric silsesquioxanes are reacted with tetraalkoxysilanes.

Claim 6 (Currently Amended): The process as claimed in ~~at least one of claims 1 to 5~~ claim 1, wherein the molar ratio of the incompletely condensed polyhedral oligomeric silsesquioxanes to the coreactant capable of hydrolytic condensation is from 1:10 to 10:1.

Claim 7 (Original): The process as claimed in claim 6, wherein the molar ratio of the incompletely condensed polyhedral oligomeric silsesquioxanes to the coreactant capable of hydrolytic condensation is 2:1.

Claim 8 (Currently Amended): The process as claimed in ~~at least one of claims 1 to 7~~ claim 1, wherein the low-k dielectric film is produced by means of a wet-chemical coating method.

Claim 9 (Original): The process as claimed in claim 8, wherein the low-k dielectric film is produced by spin coating and subsequent calcining.

Claim 10 (Currently Amended): A low-k dielectric film produced as claimed in ~~at least one of claims 1 to 9~~ claim 1.

Claim 11 (Original): The low-k dielectric film as claimed in claim 10, which has a k value of less than or equal to 2.3, measured at a frequency of 880 kHz.